

# Towards Detection and Monitoring of Ageing Precursors on the XFEL Machine Beam Control Hardware

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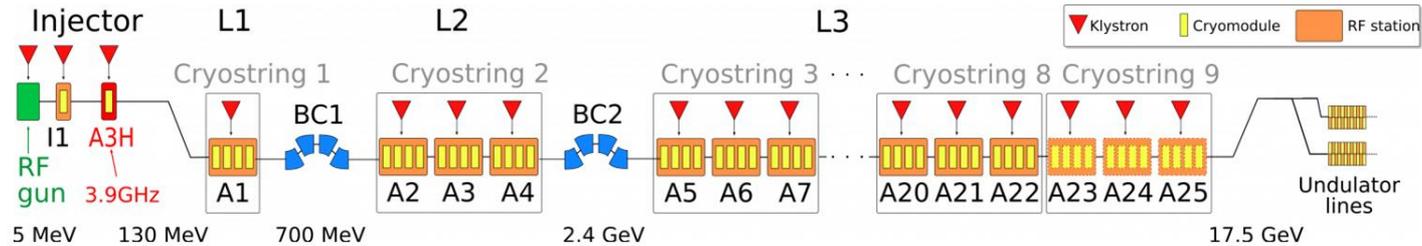
HAW Hamburg - INET Seminar 17.08.2022



- Longest superconducting linear accelerator in the world (3.4 Km)
  - 768 Niobium RF cavities over 1.7 Km
  - Maximum energy delivery of 17.4 GeV

Image: <https://xfel.desy.de/>

# European X-Ray Free-Electron Laser (XFEL) Machine Beam Control (MSK) Group

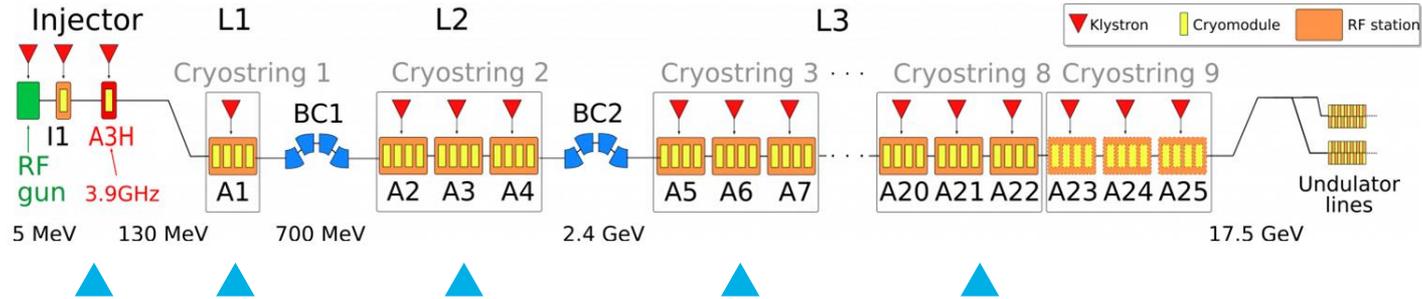


## MSK Primary Operation Sub-Groups

Figure: Julien Branlard

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## Machine Beam Control (MSK) Group

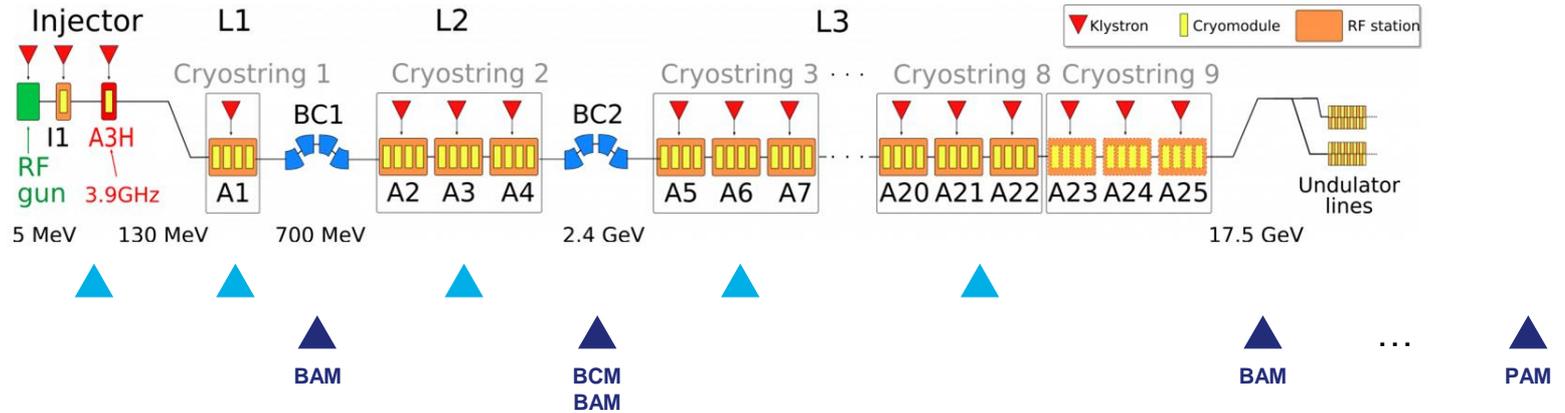


MSK Primary Operation  
Sub-Groups

Low-Level RF Control

Figure: Julien Branlard

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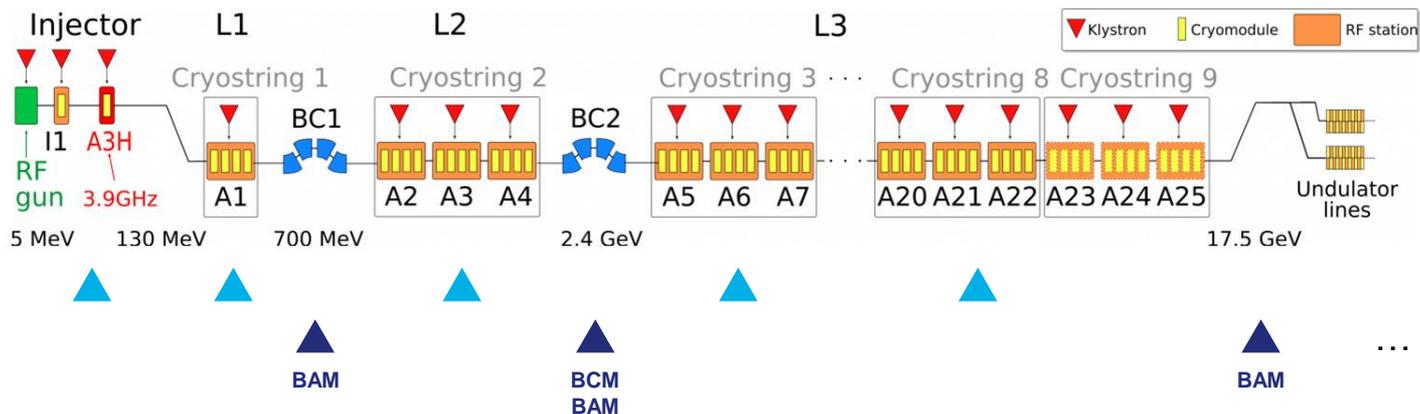
**MSK Primary Operation  
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Low-Level RF Control

Special Diagnostics

Figure: Julien Branlard

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MSK Primary Operation  
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Low-Level RF Control

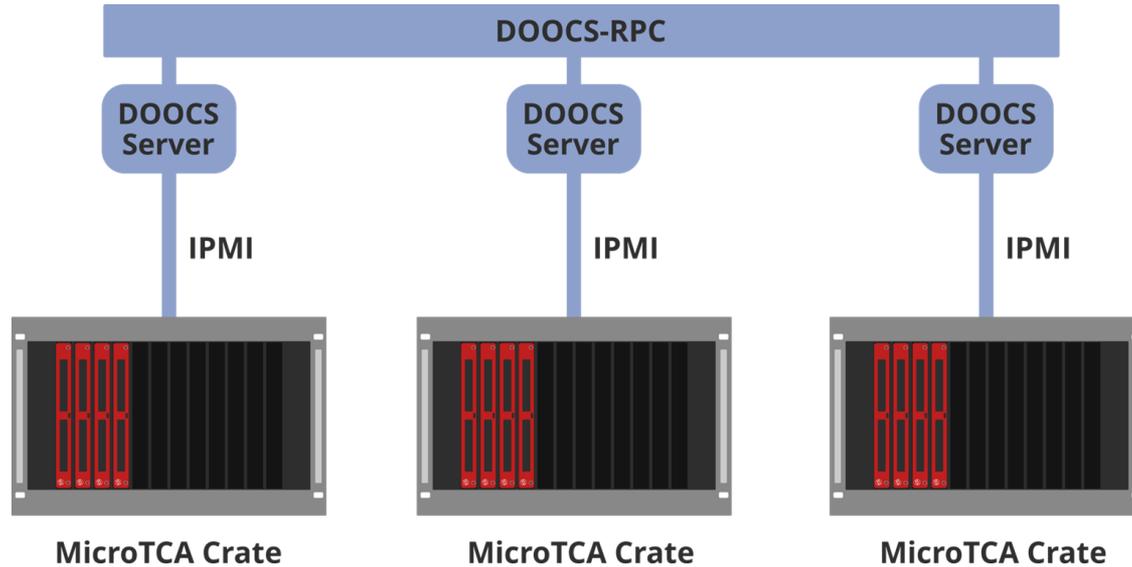
Special Diagnostics

Optical  
Synchronization

Figure: Julien Branlard

# European X-Ray Free-Electron Laser (XFEL)

## MSK Group Hardware



# European X-Ray Free-Electron Laser (XFEL)

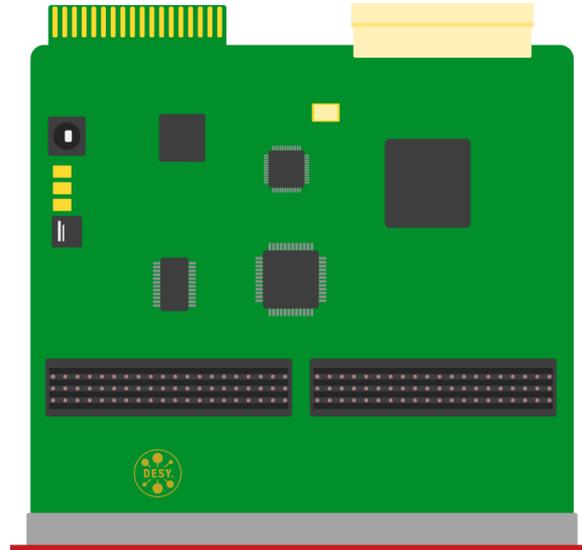
## MSK Group Hardware



MicroTCA Crate

# European X-Ray Free-Electron Laser (XFEL)

## MSK Group Hardware



**DAMC-FMC20 Carrier Board**

# European X-Ray Free-Electron Laser (XFEL) MSK Group Hardware



**FMC20**  
Carrier Board



**FMC25**  
Carrier Board



**TCK7**  
Data Processing and Telecommunication Board

and more...

Images: MicroTCA Technology Lab

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and more...

- High dependability

Images: MicroTCA Technology Lab

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- **High dependability**  $\Rightarrow$  International Electrotechnical Commission  
*“Ability to perform as and when required.”*

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“Ability to perform as and when required.”  
Reliability, Availability, Maintainability...

and more...

Images: MicroTCA Technology Lab

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- High dependability
- Long-term operation
  - Thermal Cycles
  - Enhanced Radiation

Images: MicroTCA Technology Lab

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Hardware Ageing

Images: MicroTCA Technology Lab

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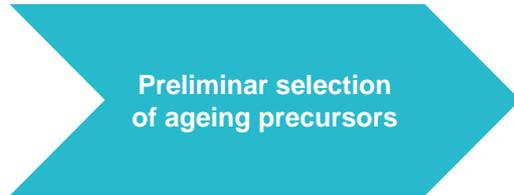


- To estimate remaining useful life
- To perform predictive maintenance

Images: MicroTCA Technology Lab

# Project Plan

## Find Relevant Features



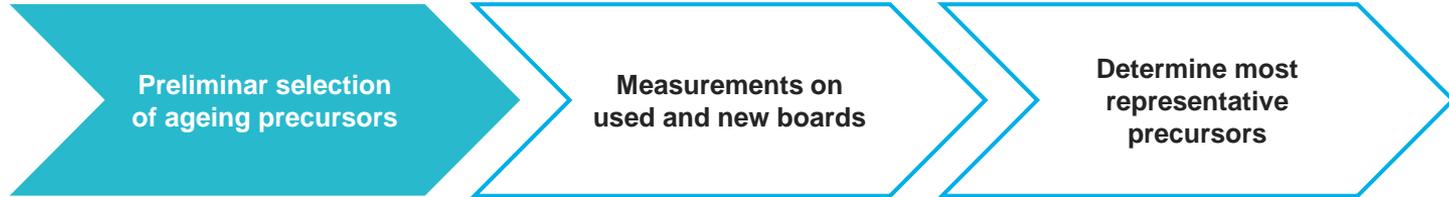
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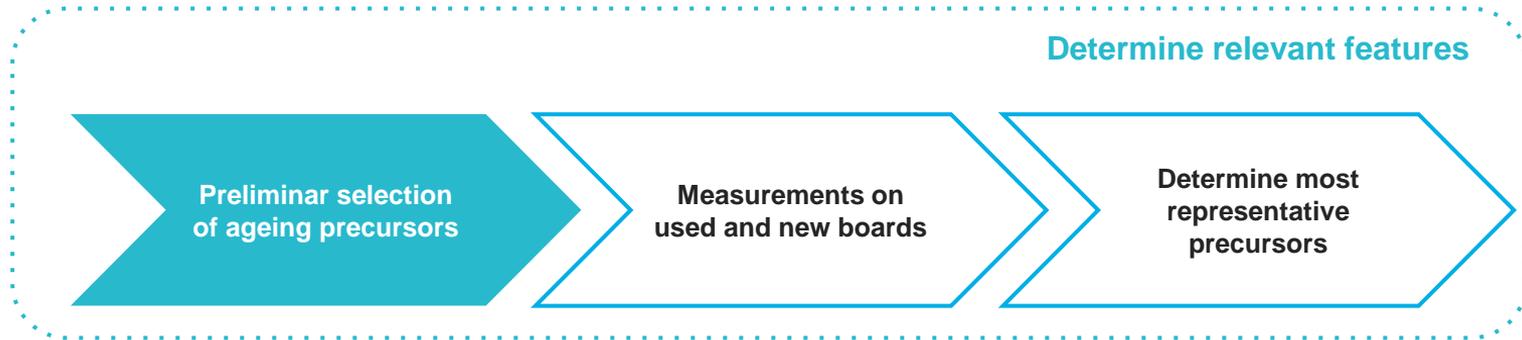
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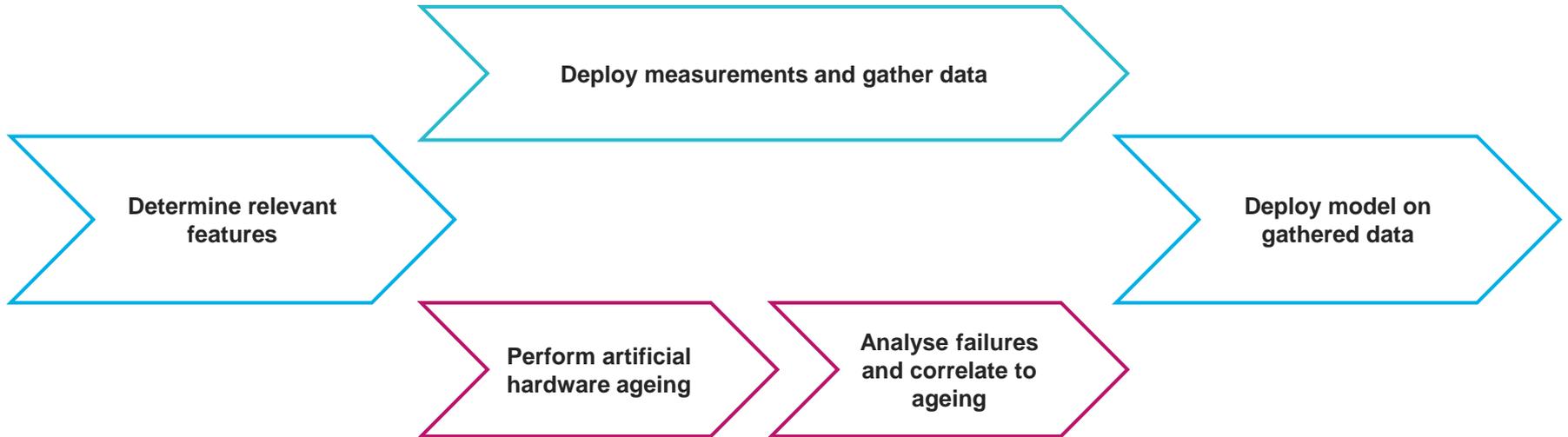
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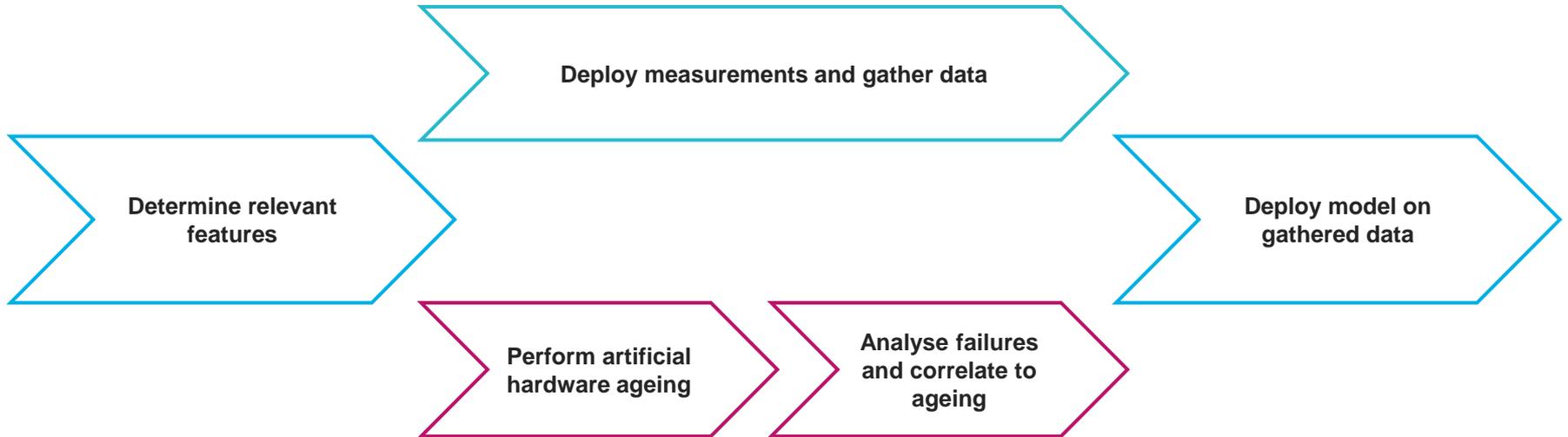
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## Overview

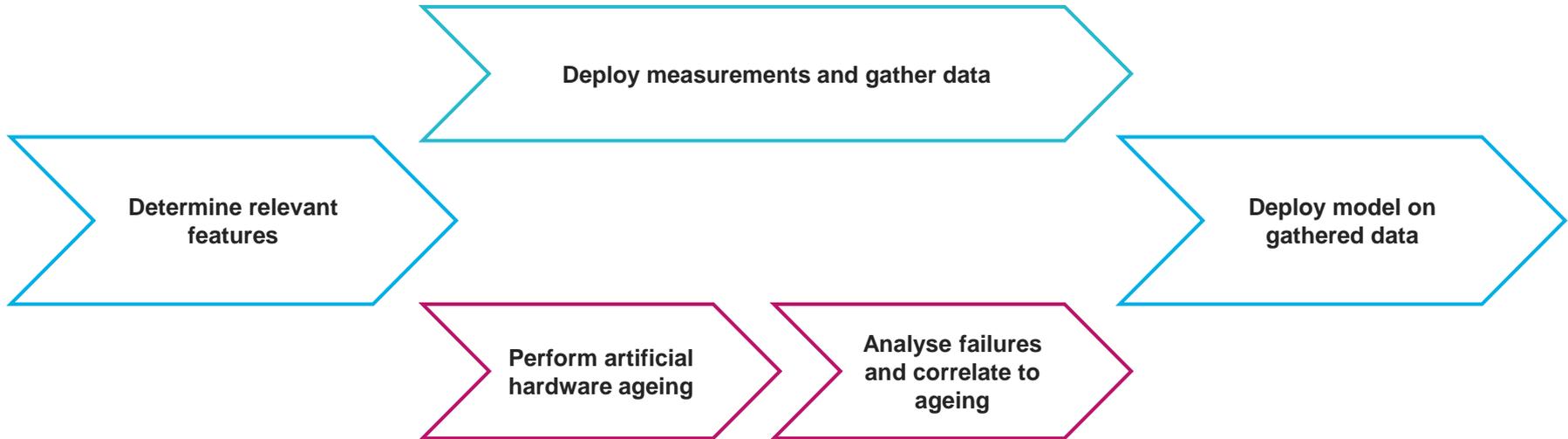


# Project Plan

## Overview



# Project Plan Overview



Problem Understanding

Relevant Data Gathering

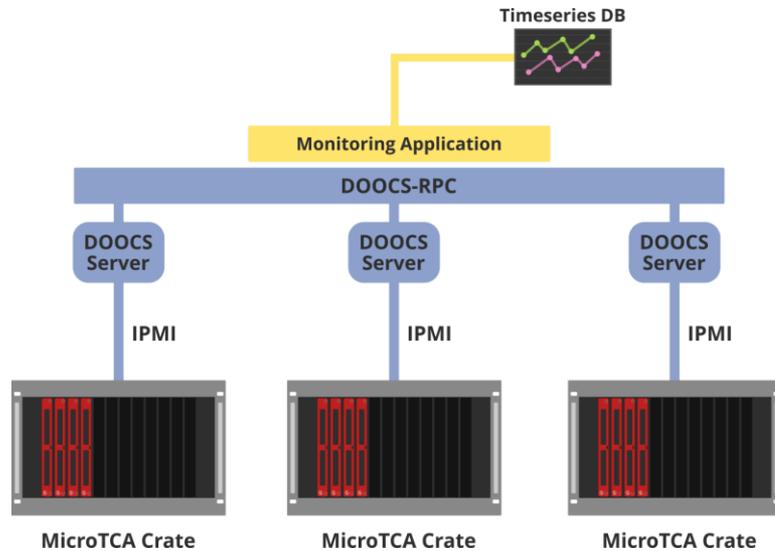
Data Cleaning & Analysis

Model Development

Model Deployment

# Ageing Precursors Monitoring

## Overview & Challenges



- **Devices**
  - Perform self-tests
  - Expose parameters on DOOCS
- **Monitoring application**
  - Collects measurements of exposed parameters
  - Stores data in a time series DB for analysis
- **Challenges**
  - Select representative ageing precursors
  - Self-tests without hardware alterations
  - No interference with running applications

# Potentially Affected Components

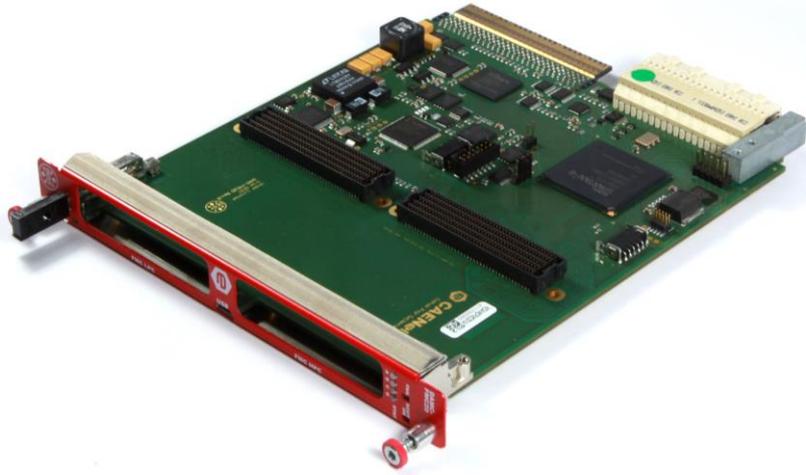
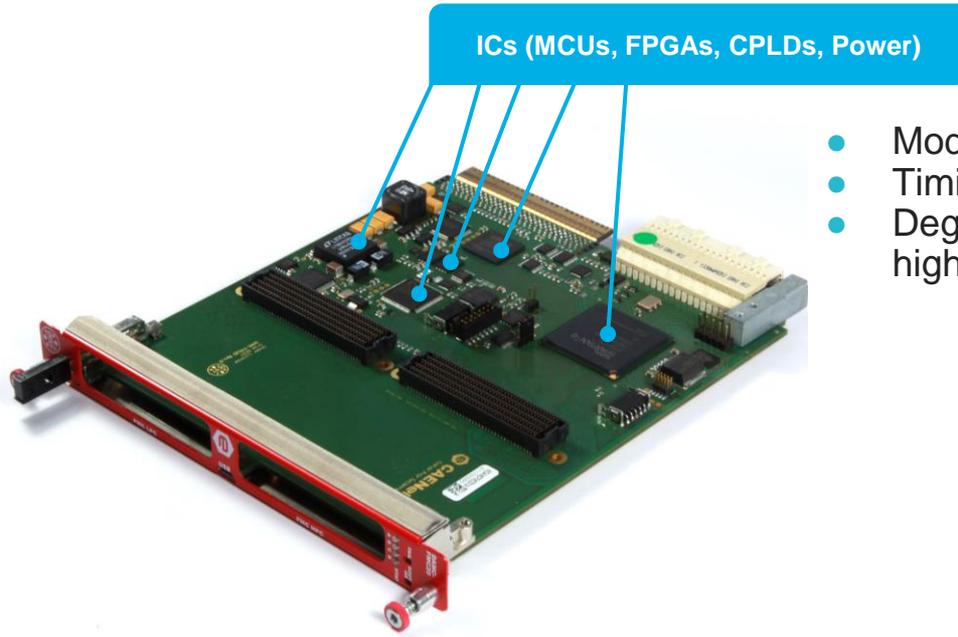


Image: MicroTCA Technology Lab

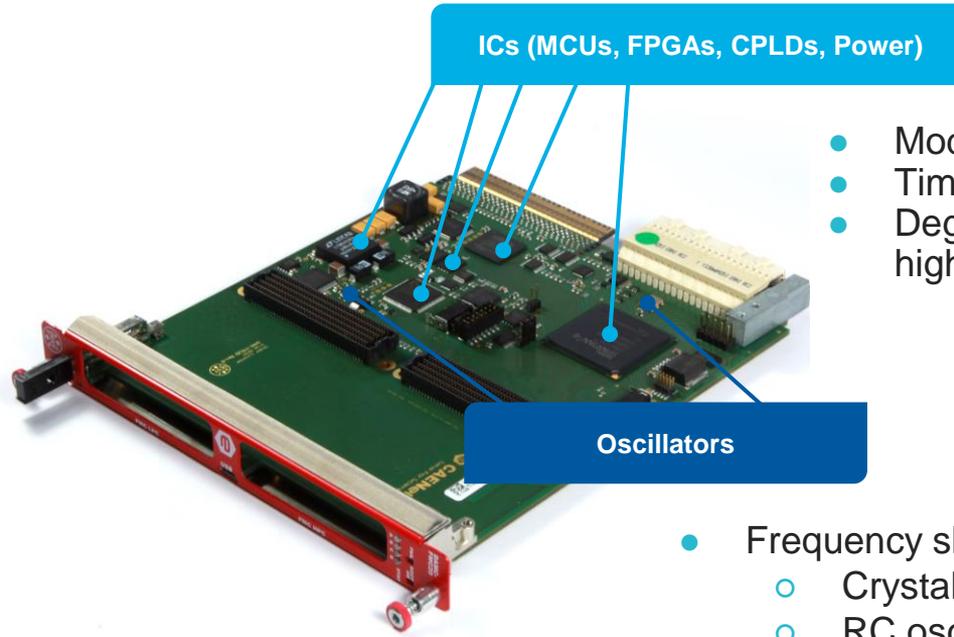
# Potentially Affected Components



- Modifications in critical paths
- Timing issues
- Degradation and reduced bandwidth of high-speed links

Image: MicroTCA Technology Lab

# Potentially Affected Components



- Modifications in critical paths
- Timing issues
- Degradation and reduced bandwidth of high-speed links

- Frequency shifting
  - Crystal oscillators
  - RC oscillators

Image: MicroTCA Technology Lab

# Ageing Mechanisms

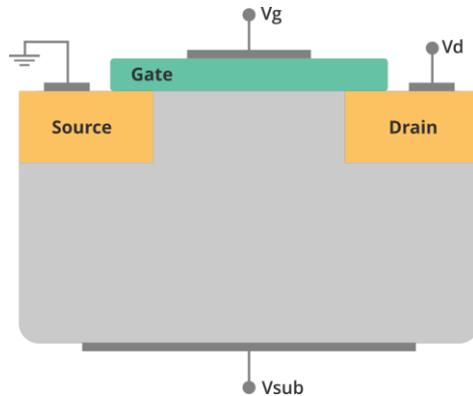
- Semiconductors
- Interconnects
- Crystals

# Ageing Mechanisms

- Semiconductors
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# Ageing Mechanisms

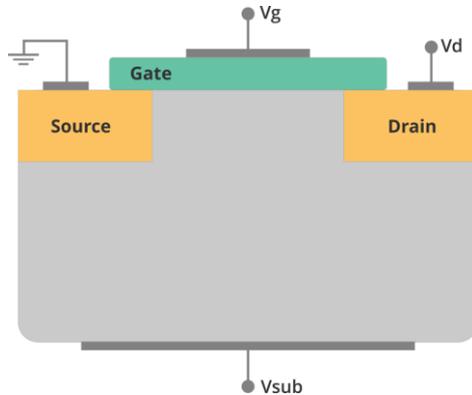
## Semiconductors



- The Metal-Oxide-Semiconductor Field-Effect Transistor (**MOSFET**) is the building-block of today's electronics
- Widely used as an electrical switch in digital electronics

# Ageing Mechanisms

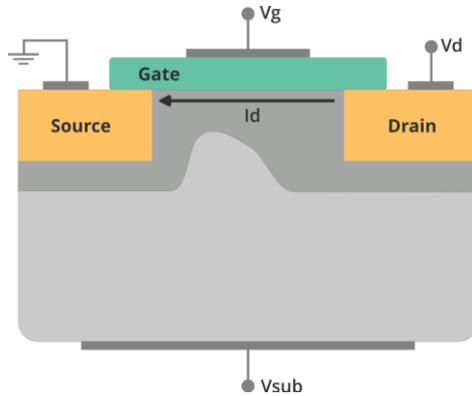
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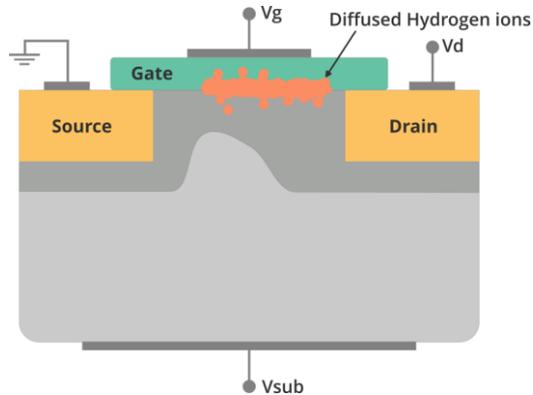
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- Widely used as an electrical switch in digital electronics
- When a voltage is applied only to the Drain ( $V_d$ ), no current passes
- When, in addition, a voltage on the Gate ( $V_g$ ) greater than a **threshold**  $V_{th}$  is applied, a channel forms allowing a current to flow.

# Ageing Mechanisms

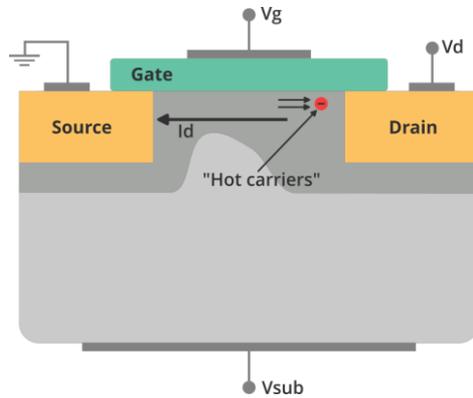
## Semiconductors - Negative Bias Temperature Instability (NBTI)



- Static mechanism affecting p-MOSFETs due to interface traps
  - **Increased**  $V_{th}$
  - **Reduced** drain current
  - **Slower switching speed**
- Partial recovery exists => degradation depends on **duty cycle**

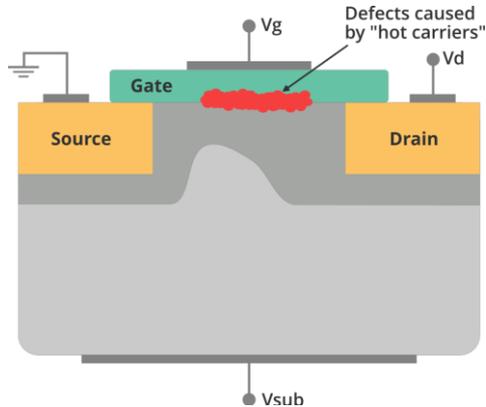
# Ageing Mechanisms

## Semiconductors - Hot Carrier Injection (HCI)



# Ageing Mechanisms

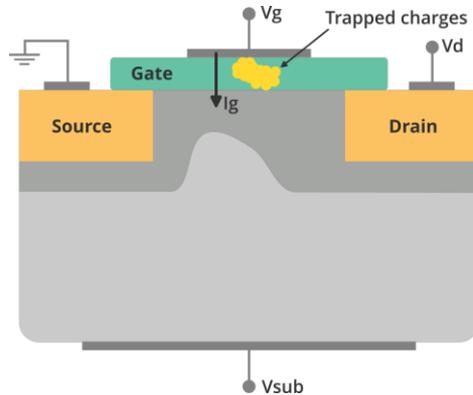
## Semiconductors - Hot Carrier Injection (HCI)



- Dynamic mechanism at high  $V_d$ 
  - **Increased  $V_{th}$**
  - **Slower switching speed**
- Has no recovery mechanism => degradation depends on **switching activity**

# Ageing Mechanisms

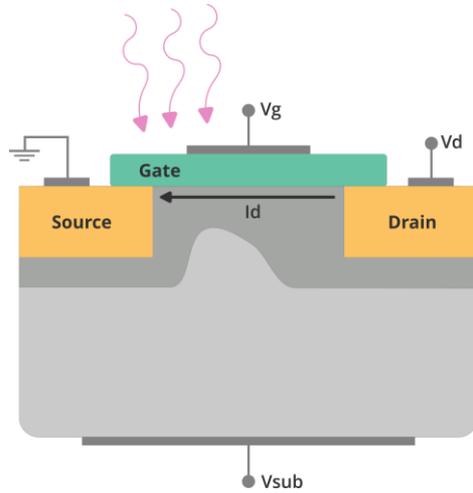
## Semiconductors - Time-Dependent Dielectric Breakdown (TDDB)



- Static mechanism due to oxide defects
  - **Increased** gate leakage current ( $I_g$ )
  - **Slower switching speed**
- Has no recovery mechanism

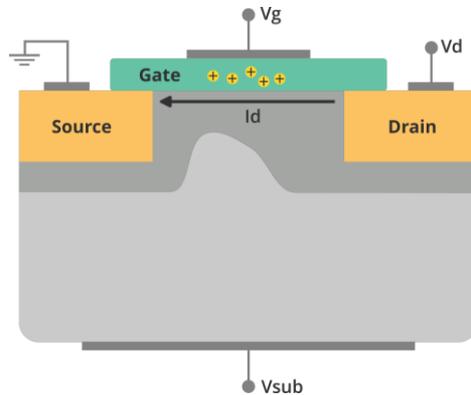
# Ageing Mechanisms

## Semiconductors - Radiation-Induced Trapped Charges

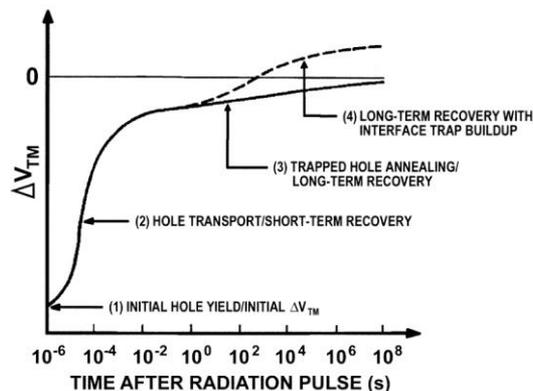


# Ageing Mechanisms

## Semiconductors - Radiation-Induced Trapped Charges



- Ionizing radiation causes positive charges to be trapped in the oxide
  - **Decreased**  $V_{th}$  => potential latch-up
- Has a slow recovery mechanism (from seconds to years)



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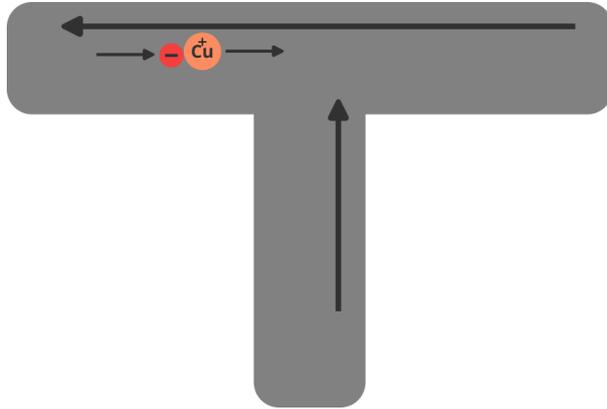
T. R. Oldham and F. B. McLean, "Total ionizing dose effects in MOS oxides and devices," in IEEE Transactions on Nuclear Science, vol. 50, no. 3, pp. 483-499, June 2003  
doi: 10.1109/TNS.2003.812927.

# Ageing Mechanisms

- Semiconductors
- Interconnects
- Crystals

# Ageing Mechanisms

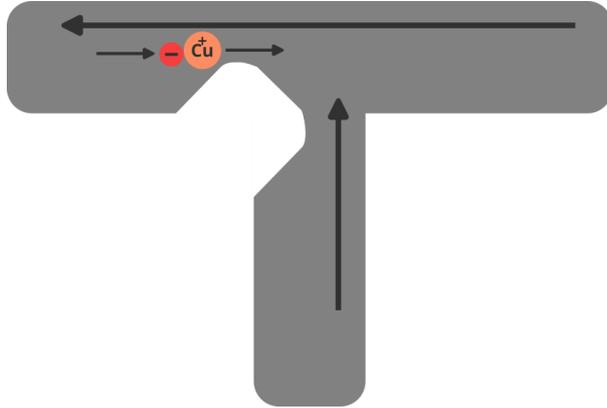
## Interconnects - Electro Migration (EM)



- Ions **migrate** due to **high current density**
  - **Increased** impedance
  - **Slower switching**
  - **Open / Short** circuits
- Has no recovery mechanism

# Ageing Mechanisms

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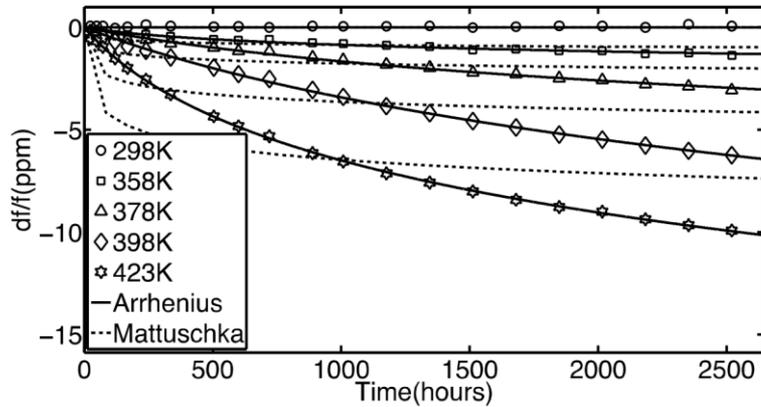
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# Ageing Mechanisms

## Quartz Crystals



- **Frequency shifting due to**
  - **Mass transfer** due to contamination
  - **Stress relief** (mounts, bonds, etc.)
  - **Radiation**
  - **Quartz degassing**



S. -y. Wang et al., "Aging models and parameters of quartz crystal resonators and oscillators," 2015 Symposium on Piezoelectricity, Acoustic Waves, and Device Applications (SPAWDA), 2015, pp. 382-385, doi: 10.1109/SPAWDA.2015.7364512.

## Sensing Ageing Effects

- Field Programmable Gate Array (FPGA)
- Microcontroller
- Static RAM (SRAM)
- Low Drop-Out Voltage Regulator
- Oscillator

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# Sensing Ageing Effects

## FPGA Propagation Delay Measurement

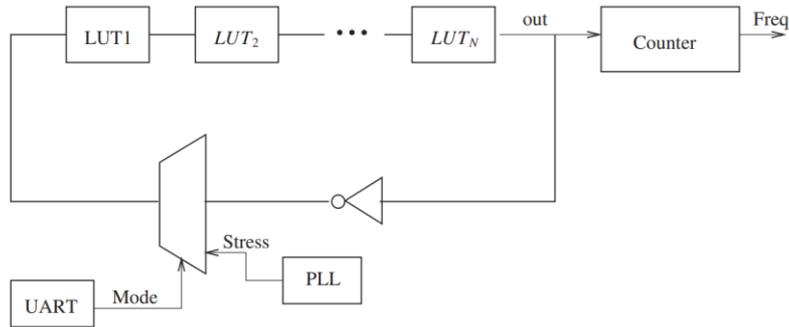


Fig. 1. RO-based sensor structure.

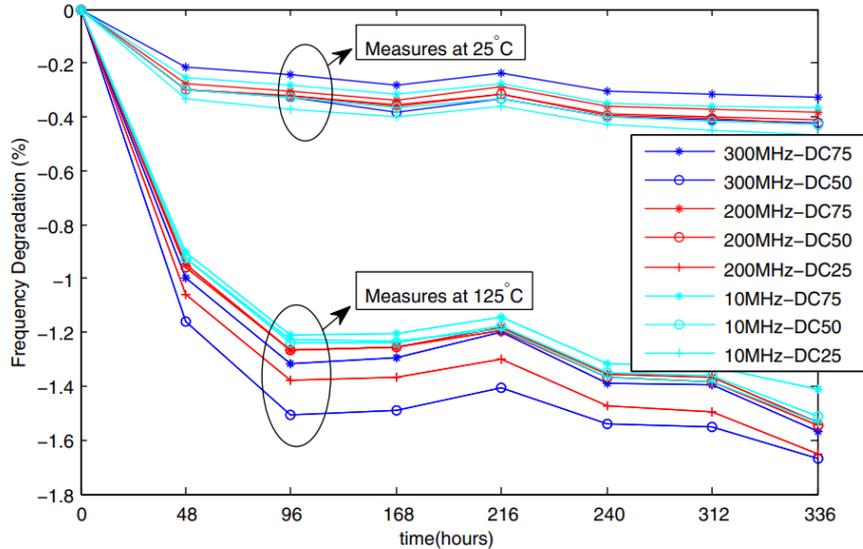
- Ring-Oscillator (RO) sensor circuit
  - Odd number of inverters
  - Frequency **proportional** to propagation delay (switching speed)
  - Artificially aged by a stress signal
- Tests conditions
  - Different temperatures
  - Varying stress signals
  - Multiple RO architectures



M. Slimani et al., "Analysis of ageing effects on ARTIX7 XILINX FPGA",  
Microelectronics Reliability, Volumes 76–77, 2017,  
pp. 168-173, doi: 10.1016/j.microrel.2017.07.006

# Sensing Ageing Effects

## FPGA Propagation Delay Impact



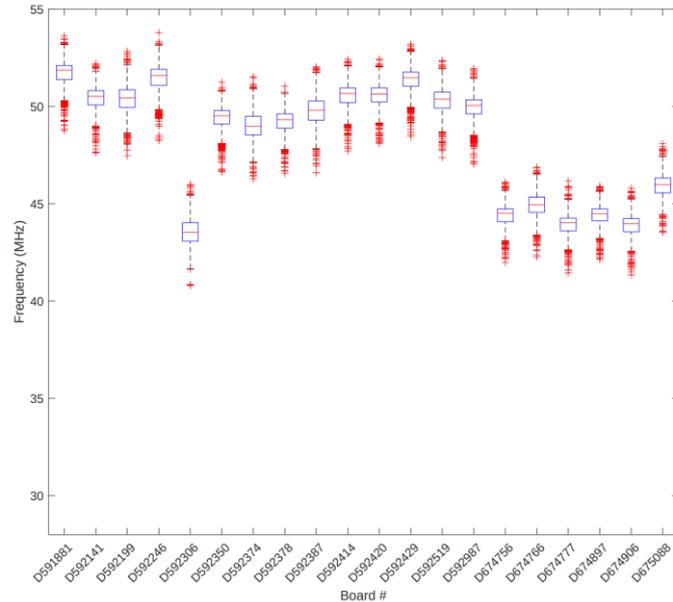
- Highly dependent on stress signal duty cycle
- More degradation at higher temperature and frequency (due to recovery)
- **Average frequency degradation of 1.7%**



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# Sensing Ageing Effects

## FPGA Propagation Delay Mapping



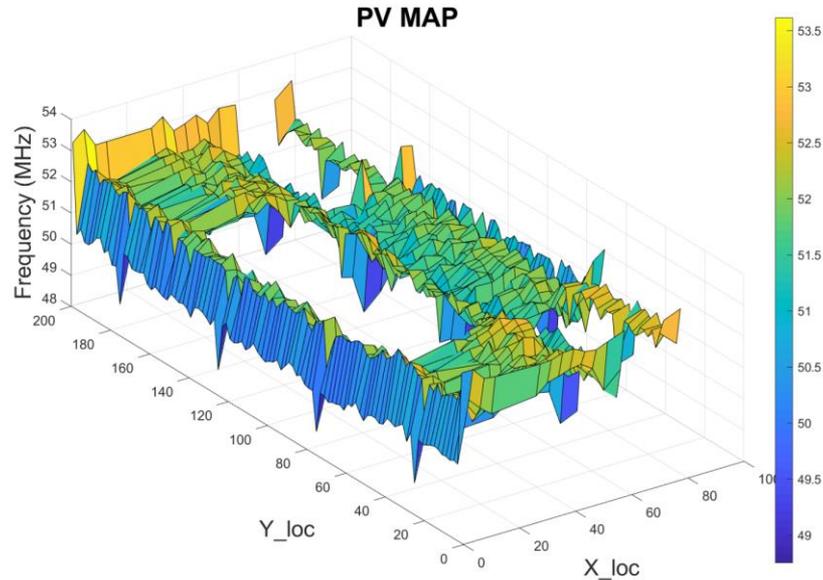
- Instantiation of multiple RO sensor circuits over the FPGA fabric at the same time
- Evaluation on multiple aged devices



P. Cheng, “Study of Monitoring Circuitry for Ageing in FPGAs”,  
Master Thesis, 2021, Department of Electrical and Information Technology,  
Lund University, Sweden

# Sensing Ageing Effects

## FPGA Propagation Delay Mapping



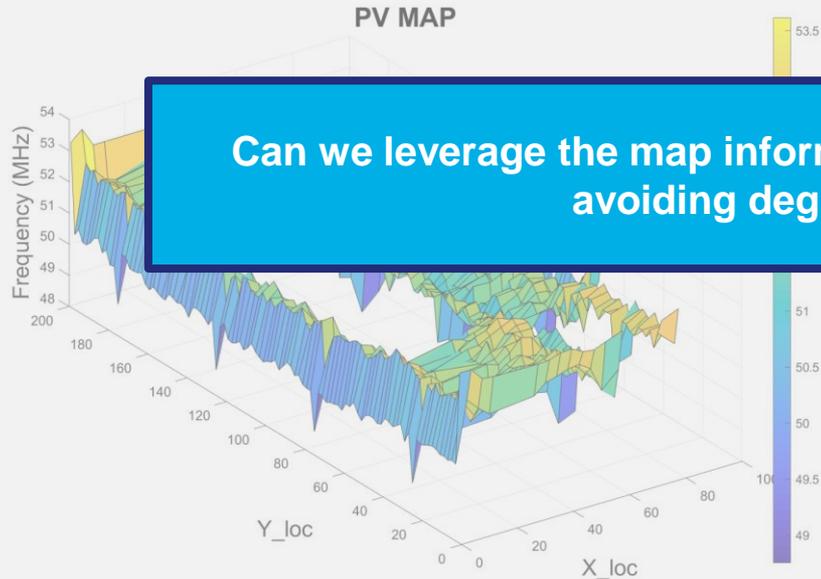
- Using placement information, a frequency degradation map can be created, by measuring individual ROs



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## FPGA Propagation Delay Mapping



Can we leverage the map information to constrain the place & route, avoiding degraded FPGA areas?

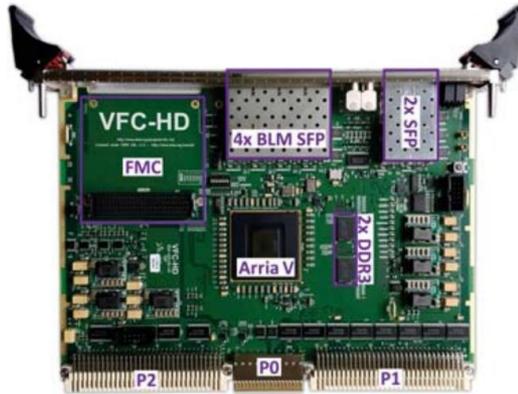
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## FPGA Optical Links Transceiver Degradation



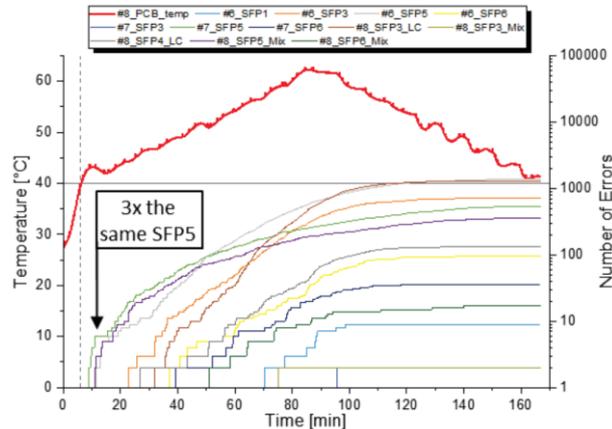
- Test and validation strategy for the new Large Hadron Collider (LHC) Beam Loss Monitor (BLM) processing module
- Optical link transceivers appeared as the weak point
  - Highly affected by operating temperature, due to degradation



V. Schramm et al., "Combined Testing And Validation Strategy For The New LHC BLM Processing Module" 2019 Annual Reliability and Maintainability Symposium (RAMS), 2019, pp. 1-7, DOI: 10.1109/RAMS.2019.8769268.

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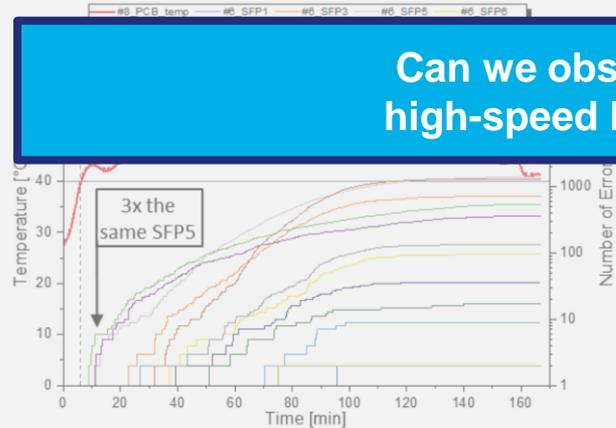


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Can we observe a degradation on the high-speed FPGA links due to ageing?



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# Sensing Ageing Effects

## FPGA Optical Links Transceiver Degradation

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Multi-Gigabit transceivers signals

Maximum DDR RAM bandwidth



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- Low Drop-Out Voltage Regulator
- Oscillator

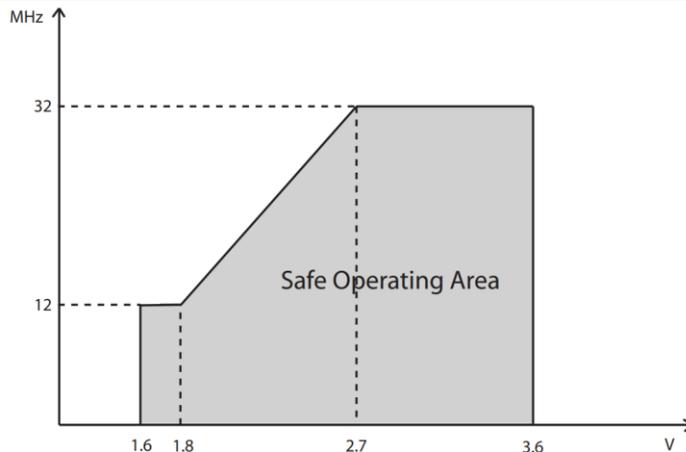
### Can we detect degraded switching speed on the MCU?

- To account for hardware ageing, vendors define bandgaps for safe operation during the guaranteed lifetime
- At lower supply voltages, the increased  $V_{th}$  may affect functionality if the clock frequency is not reduced accordingly

# Sensing Ageing Effects

## MCU Switching Speed

Can we detect degraded switching speed on the MCU?



Maximum Frequency vs.  $V_{CC}$

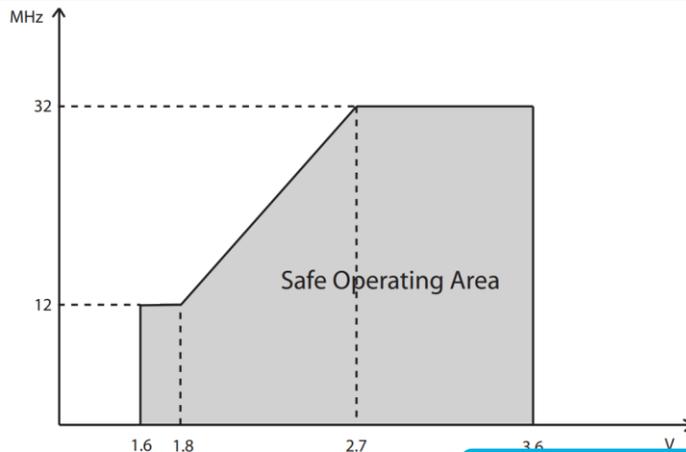
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Figure: Microchip ATxmega128A1U Data Sheet

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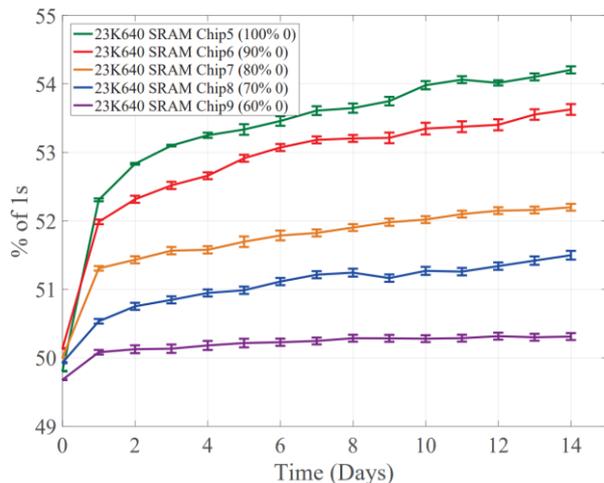
# Sensing Ageing Effects

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# Sensing Ageing Effects

## SRAM Startup Pattern



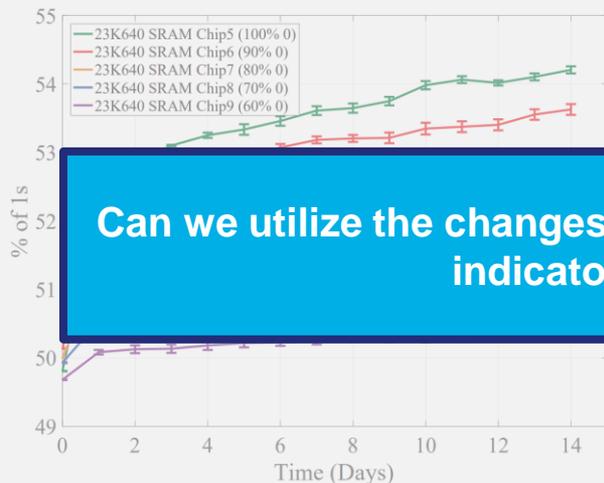
- Due to mostly balanced cells, SRAM startup value has ~50% of 1s (only affected by random fabrication process defects)
- Ageing additionally introduces a variation of  $V_{th}$ 
  - Small  $V_{th}$  difference => initial values are approximately random
  - Big  $V_{th}$  difference => initial values are biased
- After continuous stress **up to 4%** more of initial 1s



U. Guin et al., "Detecting Recycled SoCs by Exploiting Aging Induced Biases in Memory Cells"  
2019 IEEE International Symposium on Hardware Oriented Security and Trust (HOST),  
pp. 72-80, doi: 10.1109/HST.2019.8741032.

# Sensing Ageing Effects

## SRAM Startup Pattern



Can we utilize the changes of the SRAM startup pattern distribution as an indicator of MCU and FPGA ageing?

- Due to mostly balanced cells, SRAM startup value has ~50% of 1s (only affected by random fabrication process defects)

- After continuous stress **up to 4%** more of initial 1s



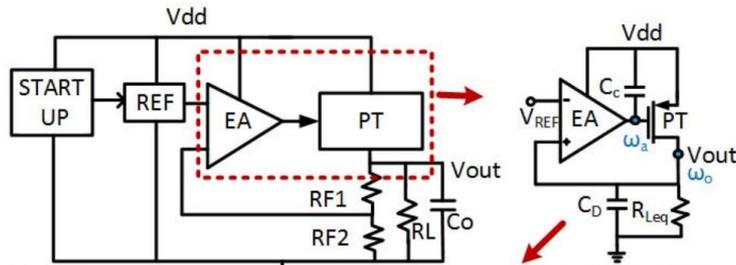
U. Guin et al., "Detecting Recycled SoCs by Exploiting Aging Induced Biases in Memory Cells" 2019 IEEE International Symposium on Hardware Oriented Security and Trust (HOST), pp. 72-80, doi: 10.1109/HST.2019.8741032.

## Sensing Ageing Effects

- Field Programmable Gate Array (FPGA)
- Microcontroller
- Static RAM (SRAM)
- Low Drop-Out Voltage Regulator
- Oscillator

# Sensing Ageing Effects

## Low drop-out (LDO) Regulators



- LDO regulators provide a constant voltage and protect from  $V_{dd}$  noise
- The Power Supply Rejection Ratio (PSRR) is the capability to suppress voltage ripples:

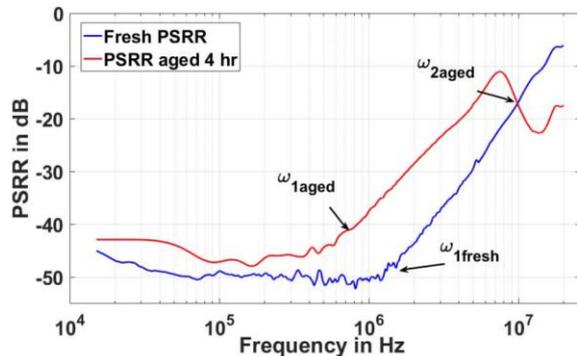
$$PSRR = 20 \log \left( \frac{v_{out}}{v_{in}} \right)$$



S. Chowdhury et al., "Aging Analysis of Low Dropout Regulator for Universal Recycled IC Detection" 2019 IEEE Computer Society Annual Symposium on VLSI (ISVLSI), pp. 604-609, doi: 10.1109/ISVLSI.2019.00113.

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  - $V_{th}$  increment
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  - Changes in capacitance and transconductance

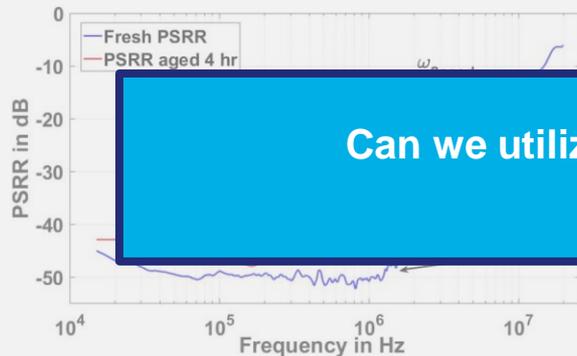


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Can we utilize the output ripple of the on-board LDOs to detect ageing effects?

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# Sensing Ageing Effects

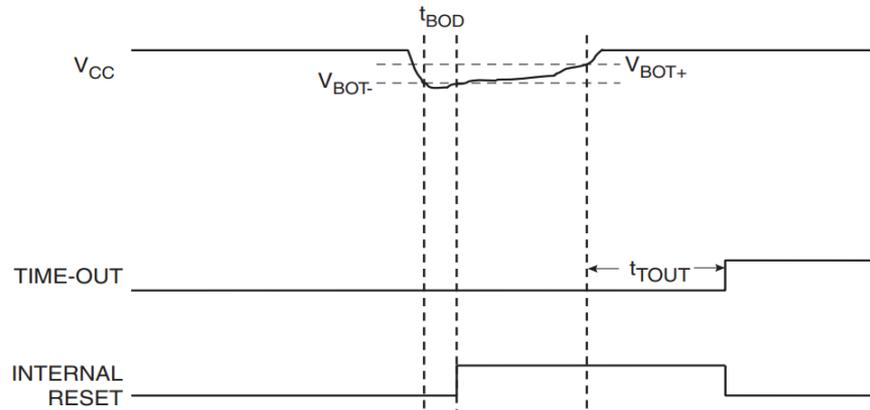
## On-Chip LDO Regulators

Can we detect PSRR degradation on the On-Chip LDO regulators?

# Sensing Ageing Effects

## On-Chip LDO Regulators

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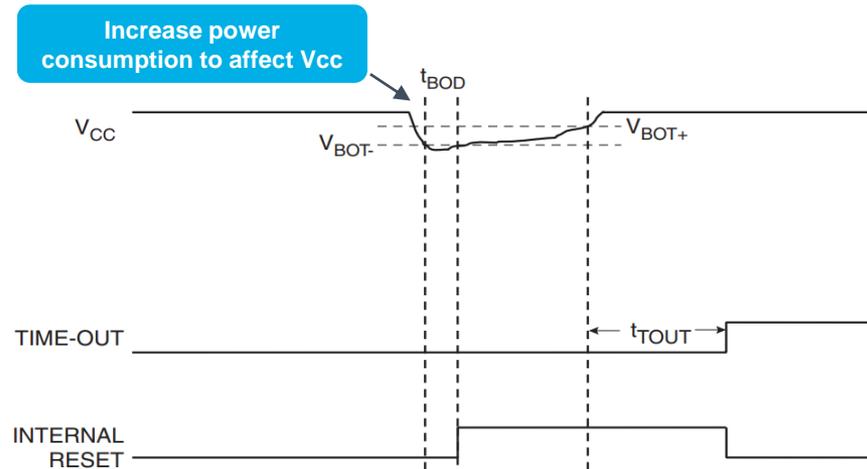
Brownout Detection Reset

Figure: Microchip XMEGA AU Manual

# Sensing Ageing Effects

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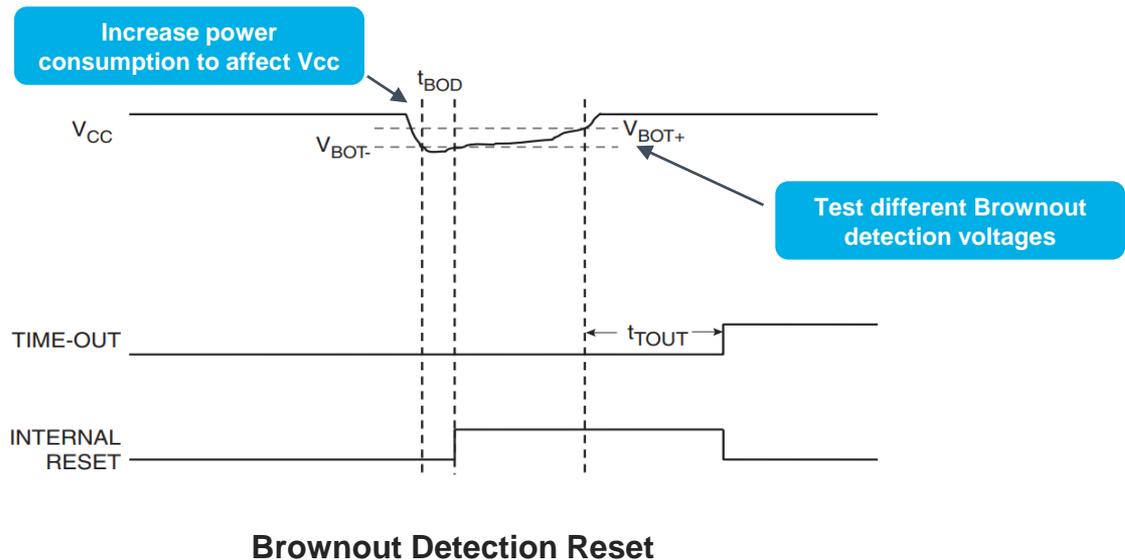


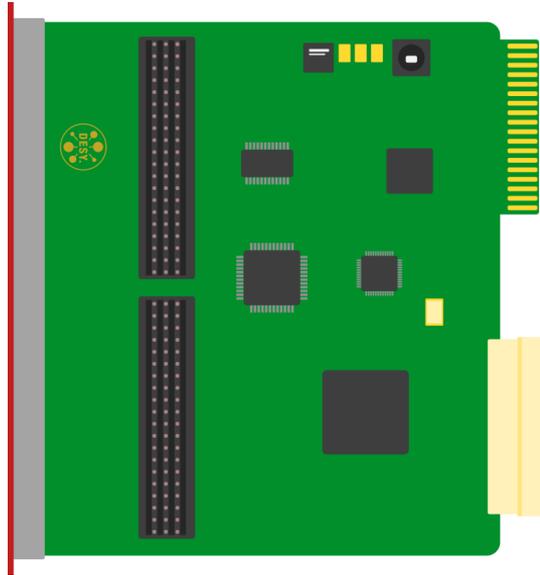
Figure: Microchip XMEGA AU Manual

# Sensing Ageing Effects

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- Microcontroller
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- Low Drop-Out Voltage Regulator
- Oscillator

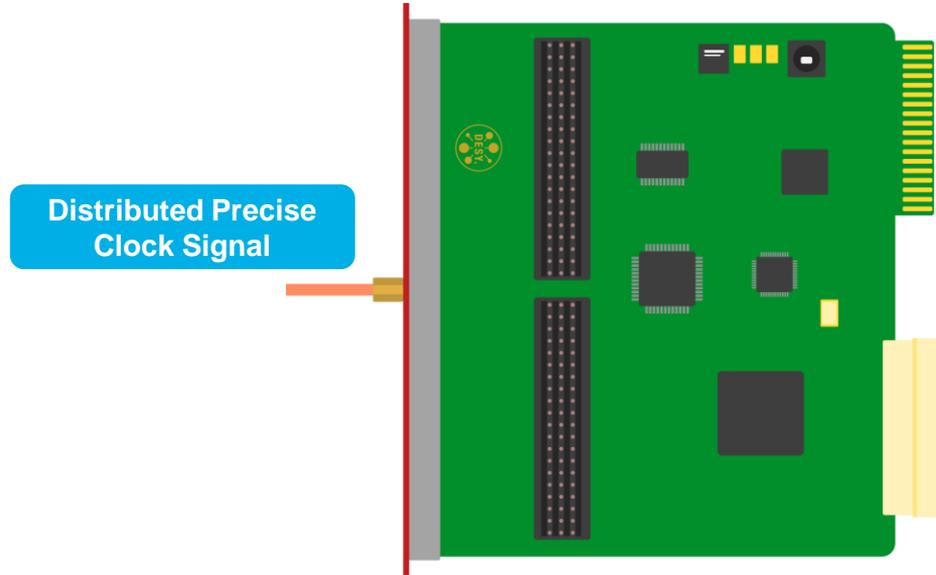
# Sensing Ageing Effects

## Oscillators Frequency Shift



# Sensing Ageing Effects

## Oscillators Frequency Shift



- Connect the external precise clock signal
- Compare crystal and internal oscillators to the known reference

- Multiple **ageing mechanisms** come into play:
  - **Silicon:** NBTI, HCI, TDDB, radiation
  - **Interconnects:** EM
  - **Crystals:** Stress relief, mass transfer, radiation

- Multiple **ageing mechanisms** come into play:
  - **Silicon:** NBTI, HCI, TDDB, radiation
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  - **Crystals:** Stress relief, mass transfer, radiation
- We plan on **assessing the overall ageing** status via:
  - Propagation delay with ring oscillators
  - High-speed links
    - Maximum FPGA-DDR bandwidth
    - Quality of FPGA MGT signals
  - Sensitivity against low voltage at high frequencies
  - Distribution of SRAM startup pattern
  - LDO regulators PSRR (external, on-chip)
  - Oscillators frequency shift (crystal and RC)

# Thank you

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